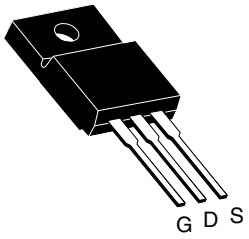
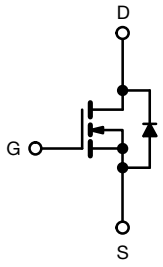
# E Series Power MOSFET

| PRODUCT SUMMARY | | |
|---|---|---|
| $V_{DS}$ (V) at $T_J$ max. | 650 | |
| $R_{DS(on)}$ max. at 25 °C (Ω) | $V_{GS}$ = 10 V | 0.125 |
| $Q_g$ max. (nC) | 130 | |
| $Q_{gs}$ (nC) | 15 | |
| $Q_{gd}$ (nC) | 39 | |
| Configuration | Single | |

**TO-220 FULLPAK**




N-Channel MOSFET

## FEATURES

- Low figure-of-merit (FOM) $R_{on}$ x $Q_g$
- Low input capacitance ($C_{iss}$)
- Reduced switching and conduction losses
- Ultra low gate charge ($Q_g$)
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

RoHS COMPLIANT

HALOGEN FREE Available

## APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
  - High-intensity discharge (HID)
  - Fluorescent ballast lighting
  - LED lighting
- Industrial
  - Welding
  - Induction heating
  - Motor drives
- Battery chargers
- Renewable energy
  - Solar (PV inverters)

| ORDERING INFORMATION | |
|---|---|
| Package | TO-220 FULLPAK |
| Lead (Pb)-free and Halogen-free | SiHF30N60E-GE3 |
| Lead (Pb)-free | SiHF30N60E-E3 |

**ABSOLUTE MAXIMUM RATINGS** ($T_C$ = 25 °C, unless otherwise noted)

| PARAMETER | | | SYMBOL | LIMIT | UNIT |
|---|---|---|---|---|---|
| Drain-Source Voltage | | | $V_{DS}$ | 600 | V |
| Gate-Source Voltage | | | $V_{GS}$ | ± 30 | |
| Continuous Drain Current ($T_J$ = 150 °C) [d] | $V_{GS}$ at 10 V | $T_C$ = 25 °C | $I_D$ | 29 | A |
| | | $T_C$ = 100 °C | | 18 | |
| Pulsed Drain Current [a] | | | $I_{DM}$ | 76 | |
| Linear Derating Factor | | | | 0.29 | W/°C |
| Single Pulse Avalanche Energy [b] | | | $E_{AS}$ | 690 | mJ |
| Maximum Power Dissipation | | | $P_D$ | 37 | W |
| Operating Junction and Storage Temperature Range | | | $T_J$, $T_{stg}$ | -55 to +150 | °C |
| Drain-Source Voltage Slope | $V_{DS}$ = 0 V to 80 % $V_{DS}$ | | dV/dt | 70 | V/ns |
| Reverse Diode dV/dt [e] | | | | 18 | |
| Soldering Recommendations (Peak temperature) [c] | for 10 s | | | 300 | °C |
| Mounting Torque | M3 screw | | | 0.6 | Nm |

**Notes**

a. Repetitive rating; pulse width limited by maximum junction temperature.
b. $V_{DD}$ = 50 V, starting $T_J$ = 25 °C, L = 28.2 mH, $R_g$ = 25 Ω, $I_{AS}$ = 7 A.
c. 1.6 mm from case.
d. Limited by maximum junction temperature.
e. $I_{SD} \leq I_D$, dI/dt = 100 A/µs, starting $T_J$ = 25 °C.

## THERMAL RESISTANCE RATINGS

| PARAMETER | SYMBOL | TYP. | MAX. | UNIT |
|---|---|---|---|---|
| Maximum Junction-to-Ambient | $R_{thJA}$ | - | 65 | °C/W |
| Maximum Junction-to-Case (Drain) | $R_{thJC}$ | - | 3.4 | |

## SPECIFICATIONS ($T_J$ = 25 °C, unless otherwise noted)

| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|---|---|---|---|---|---|---|
| **Static** | | | | | | |
| Drain-Source Breakdown Voltage | $V_{DS}$ | $V_{GS}$ = 0 V, $I_D$ = 250 µA | 600 | - | - | V |
| $V_{DS}$ Temperature Coefficient | $\Delta V_{DS}/T_J$ | Reference to 25 °C, $I_D$ = 250 µA | - | 0.64 | - | V/°C |
| Gate-Source Threshold Voltage (N) | $V_{GS(th)}$ | $V_{DS}$ = $V_{GS}$, $I_D$ = 250 µA | 2.0 | 2.8 | 4.0 | V |
| Gate-Source Leakage | $I_{GSS}$ | $V_{GS}$ = ± 20 V | - | - | ± 100 | nA |
| | | $V_{GS}$ = ± 30 V | - | - | ± 1 | µA |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$ = 600 V, $V_{GS}$ = 0 V | - | - | 1 | µA |
| | | $V_{DS}$ = 600 V, $V_{GS}$ = 0 V, $T_J$ = 150 °C | - | - | 100 | |
| Drain-Source On-State Resistance | $R_{DS(on)}$ | $V_{GS}$ = 10 V, $I_D$ = 15 A | - | 0.104 | 0.125 | Ω |
| Forward Transconductance[a] | $g_{fs}$ | $V_{DS}$ = 8 V, $I_D$ = 3 A | - | 5.4 | - | S |
| **Dynamic** | | | | | | |
| Input Capacitance | $C_{iss}$ | $V_{GS}$ = 0 V, $V_{DS}$ = 100 V, f = 1.0 MHz | - | 2600 | - | pF |
| Output Capacitance | $C_{oss}$ | | - | 138 | - | |
| Reverse Transfer Capacitance | $C_{rss}$ | | - | 3 | - | |
| Effective Output Capacitance, Energy Related [a] | $C_{o(er)}$ | $V_{DS}$ = 0 V to 480 V, $V_{GS}$ = 0 V | - | 98 | - | |
| Effective Output Capacitance, Time Related [b] | $C_{o(tr)}$ | | - | 346 | - | |
| Total Gate Charge | $Q_g$ | $V_{GS}$ = 10 V; $I_D$ = 15 A, $V_{DS}$ = 480 V | - | 85 | 130 | nC |
| Gate-Source Charge | $Q_{gs}$ | | - | 15 | - | |
| Gate-Drain Charge | $Q_{gd}$ | | - | 39 | - | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD}$ = 380 V, $I_D$ = 15 A, $V_{GS}$ = 10 V, $R_g$ = 4.7 Ω | - | 19 | 40 | ns |
| Rise Time | $t_r$ | | - | 32 | 65 | |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 63 | 95 | |
| Fall Time | $t_f$ | | - | 36 | 75 | |
| Gate Input Resistance | $R_g$ | f = 1 MHz, open drain | - | 0.63 | - | Ω |
| **Drain-Source Body Diode Characteristics** | | | | | | |
| Continuous Source-Drain Diode Current | $I_S$ | MOSFET symbol showing the integral reverse p - n junction diode  | - | - | 29 | A |
| Pulsed Diode Forward Current | $I_{SM}$ | | - | - | 65 | |
| Diode Forward Voltage | $V_{SD}$ | $T_J$ = 25 °C, $I_S$ = 15 A, $V_{GS}$ = 0 V | - | - | 1.3 | V |
| Body Diode Reverse Recovery Time | $t_{rr}$ | $T_J$ = 25 °C, $I_F$ = $I_S$ = 15 A, dI/dt = 100 A/µs, $V_R$ = 20 V | - | 402 | 605 | ns |
| Body Diode Reverse Recovery Charge | $Q_{rr}$ | | - | 7 | 15 | µC |
| Reverse Recovery Current | $I_{RRM}$ | | - | 32 | 65 | A |

**Notes**

a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as $C_{oss}$ while $V_{DS}$ is rising from 0 % to 80 % $V_{DSS}$.

b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as $C_{oss}$ while $V_{DS}$ is rising from 0 % to 80 % $V_{DSS}$.

## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

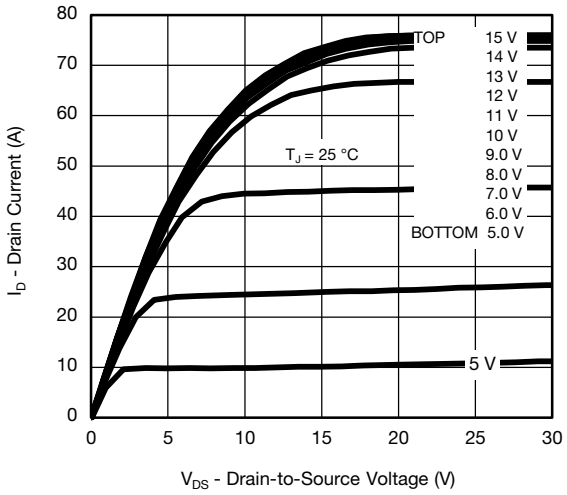



**Fig. 1 - Typical Output Characteristics, $T_C$ = 25 °C**

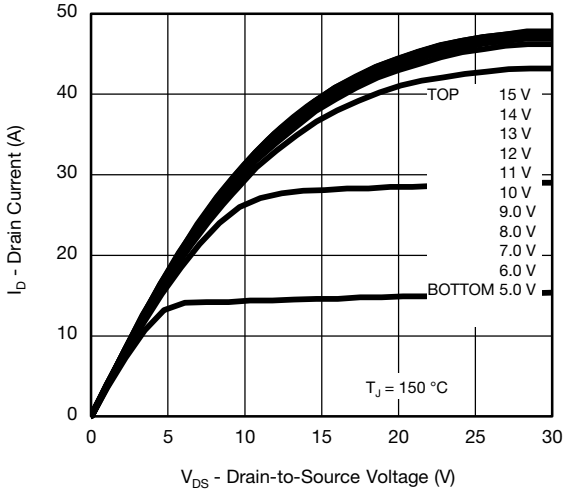



**Fig. 2 - Typical Output Characteristics, $T_C$ = 150 °C**

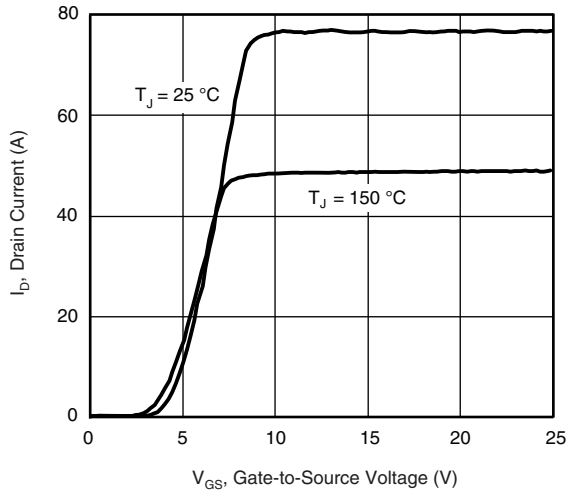



**Fig. 3 - Typical Transfer Characteristics**

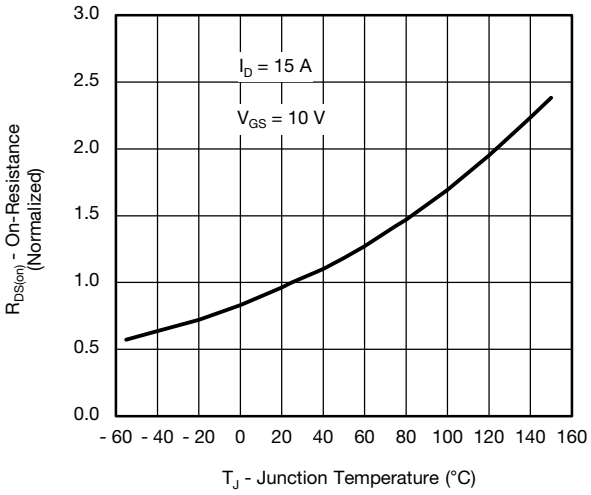



**Fig. 4 - Normalized On-Resistance vs. Temperature**

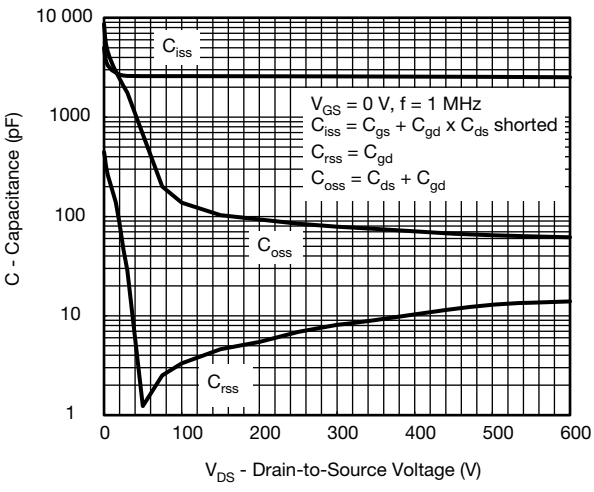



**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**

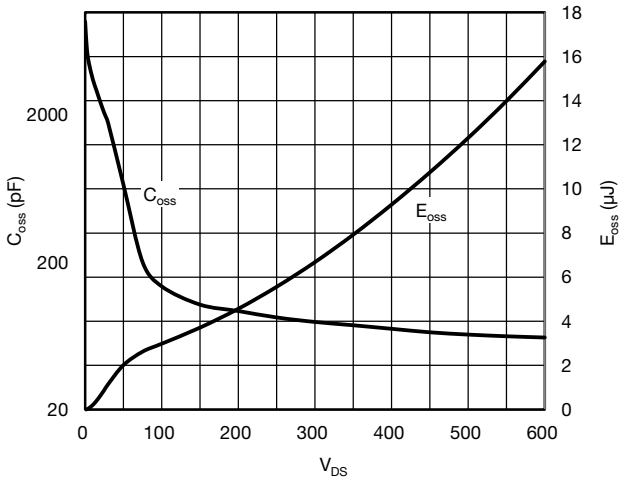



**Fig. 6 - $C_{oss}$ and $E_{oss}$ vs. $V_{DS}$**

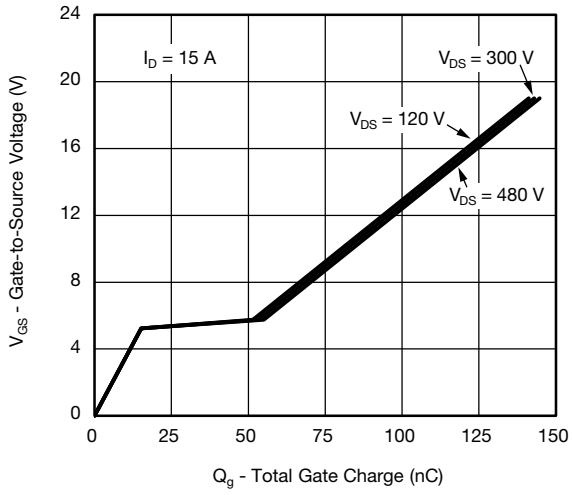



**Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage**

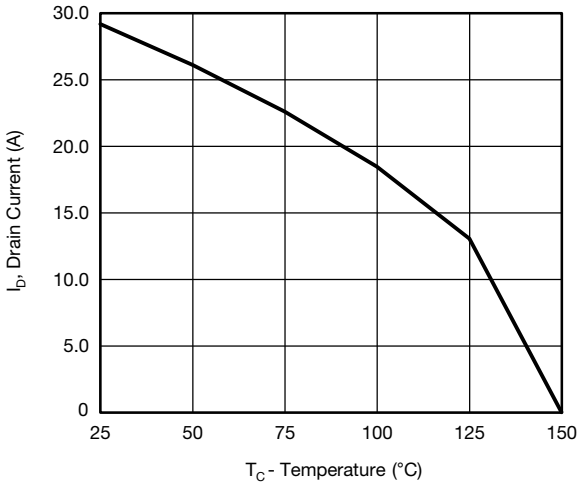



**Fig. 10 - Maximum Drain Current vs. Case Temperature**

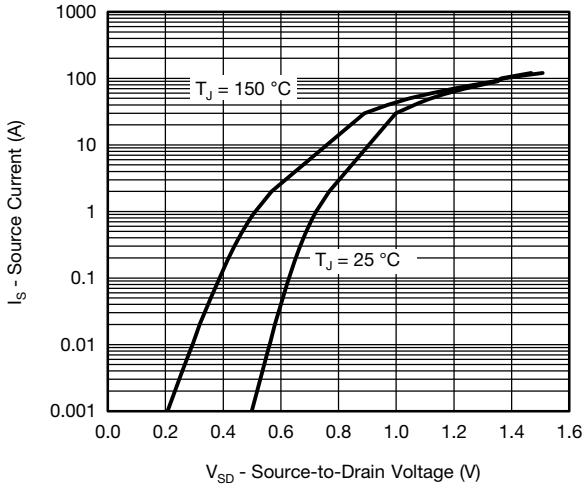



**Fig. 8 - Typical Source-Drain Diode Forward Voltage**

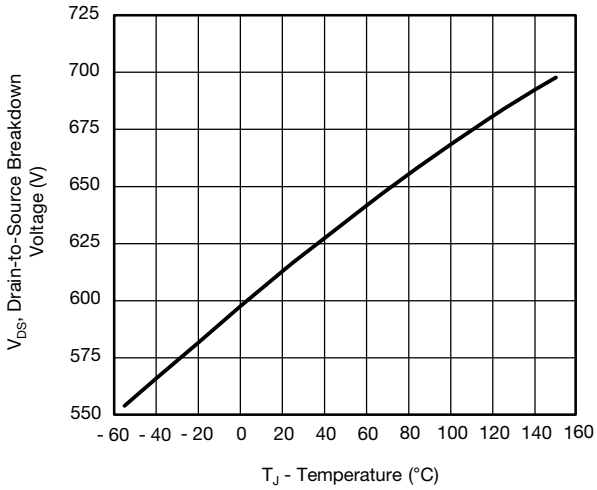



**Fig. 11 - Temperature vs. Drain-to-Source Voltage**

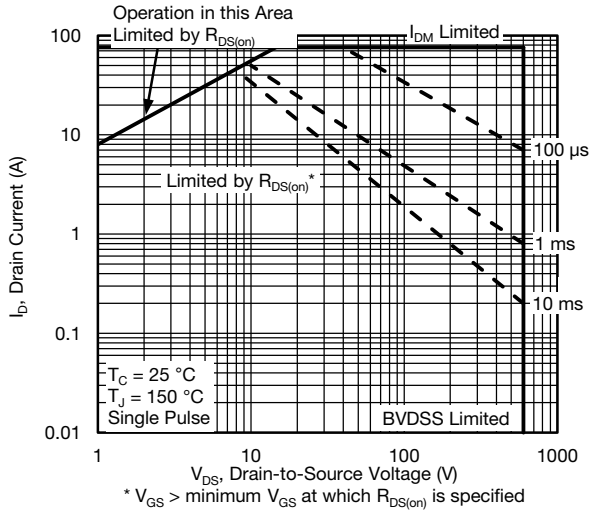



**Fig. 9 - Maximum Safe Operating Area**

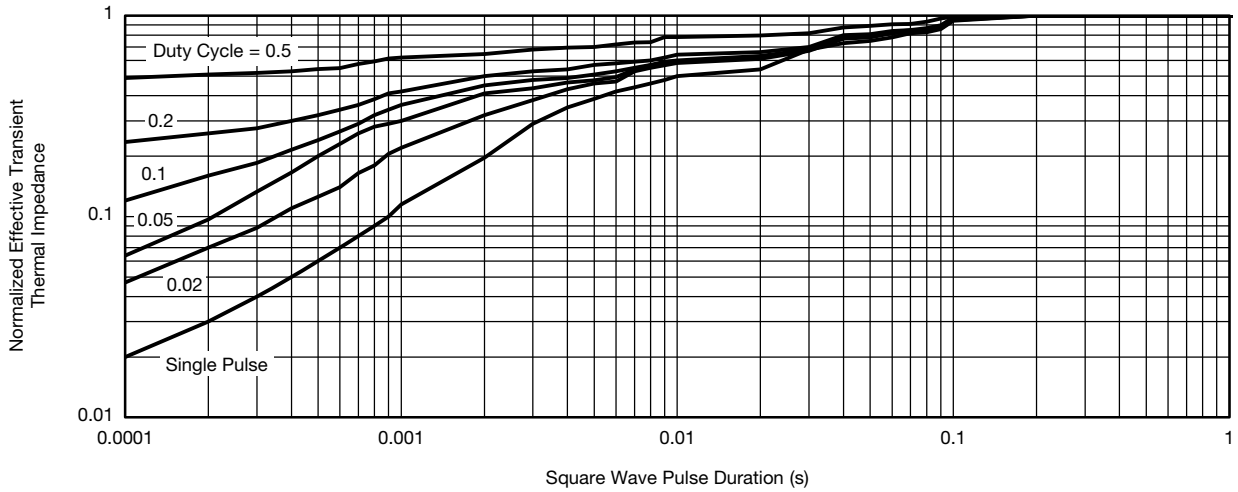



**Fig. 12 - Normalized Thermal Transient Impedance, Junction-to-Case**

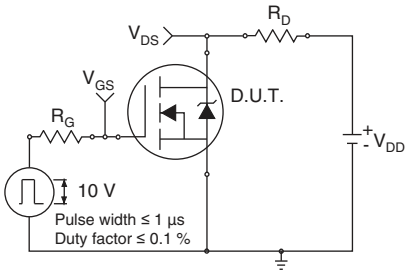



**Fig. 13 - Switching Time Test Circuit**

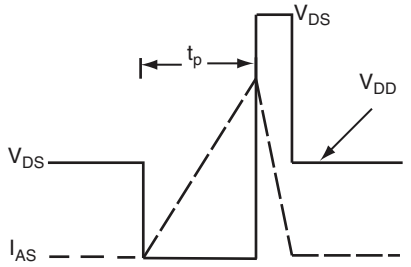



**Fig. 16 - Unclamped Inductive Waveforms**

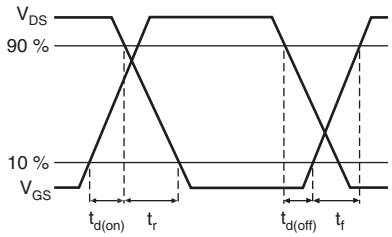



**Fig. 14 - Switching Time Waveforms**

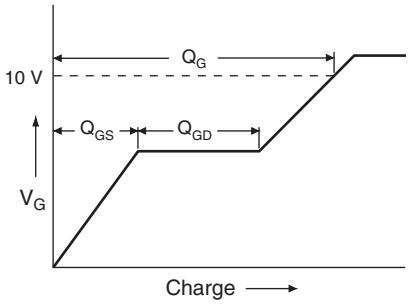



**Fig. 17 - Basic Gate Charge Waveform**

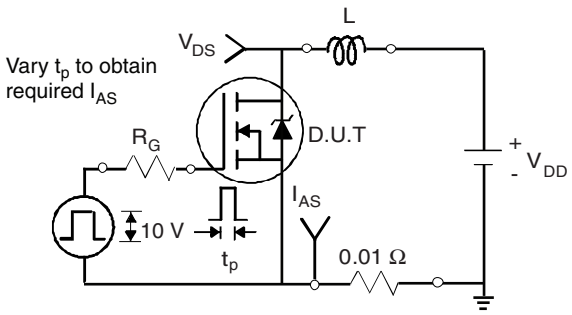



**Fig. 15 - Unclamped Inductive Test Circuit**

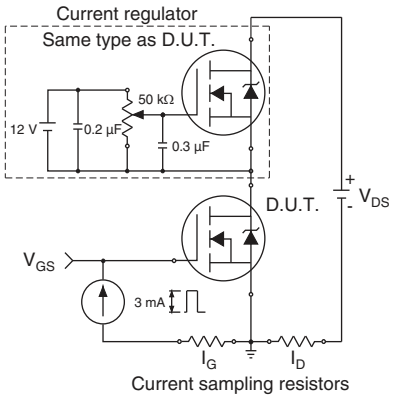
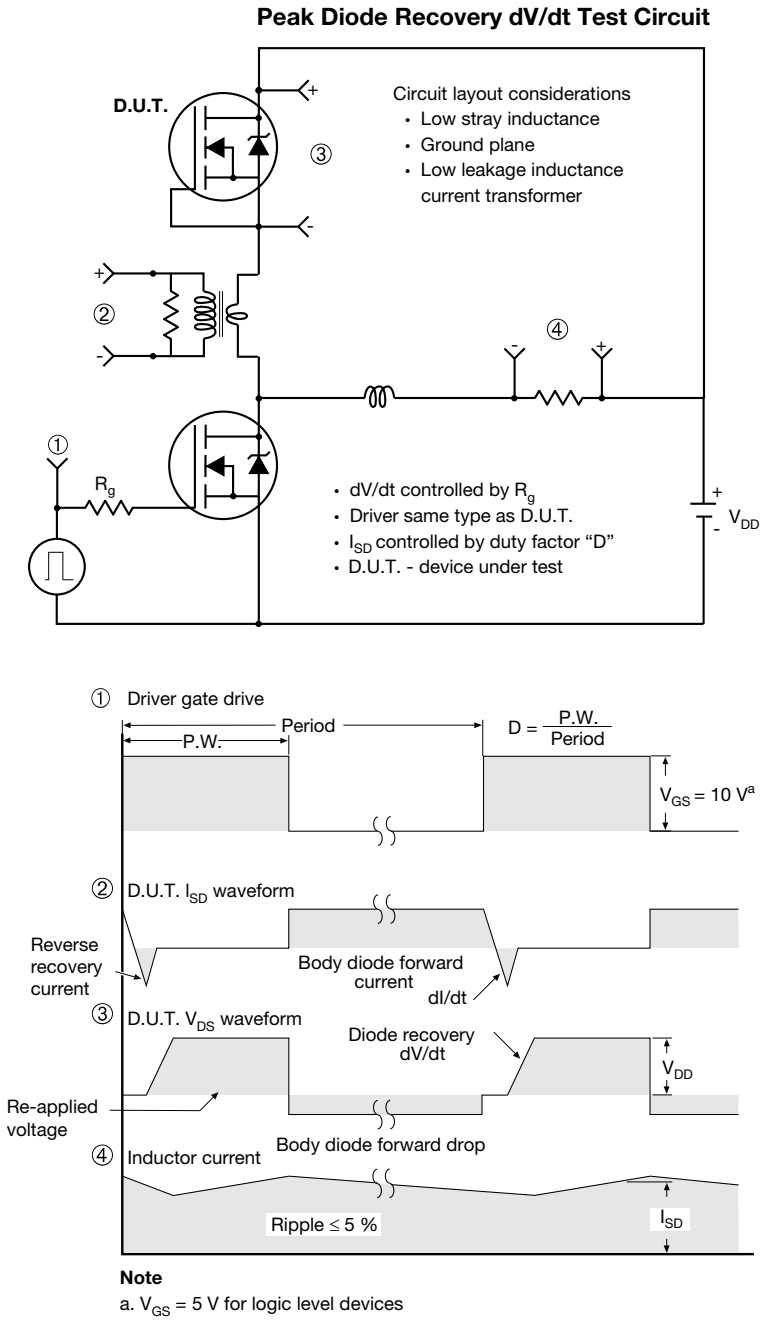



**Fig. 18 - Gate Charge Test Circuit**




**Note**

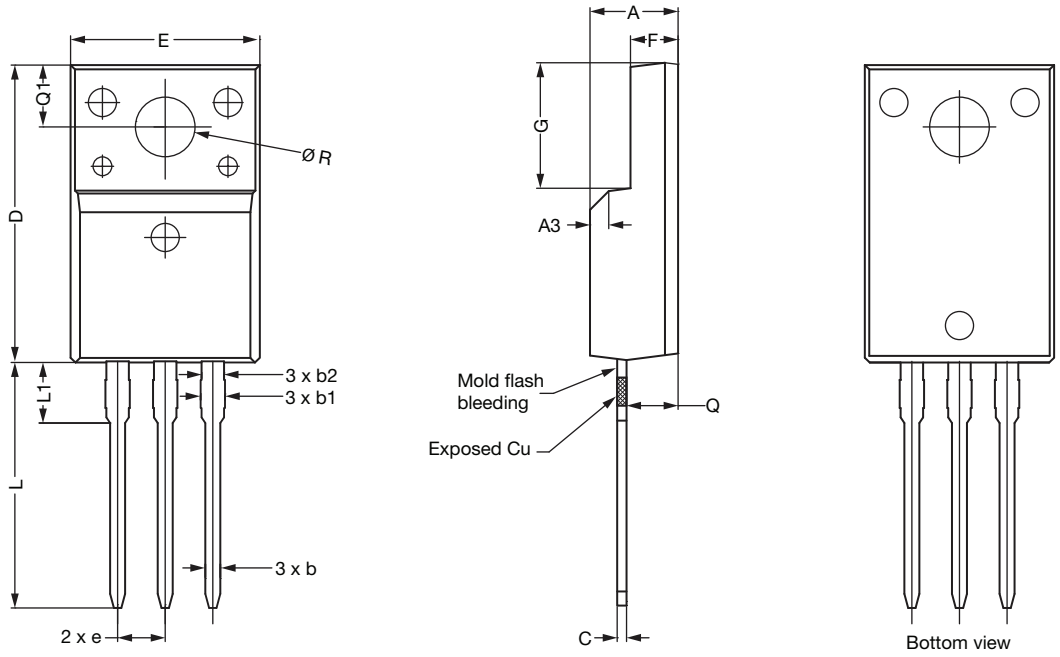
a. $V_{GS}$ = 5 V for logic level devices

**Fig. 19 - For N-Channel**

*Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?91454.*

# TO-220 FULLPAK (High Voltage)

## OPTION 1: FACILITY CODE = 9

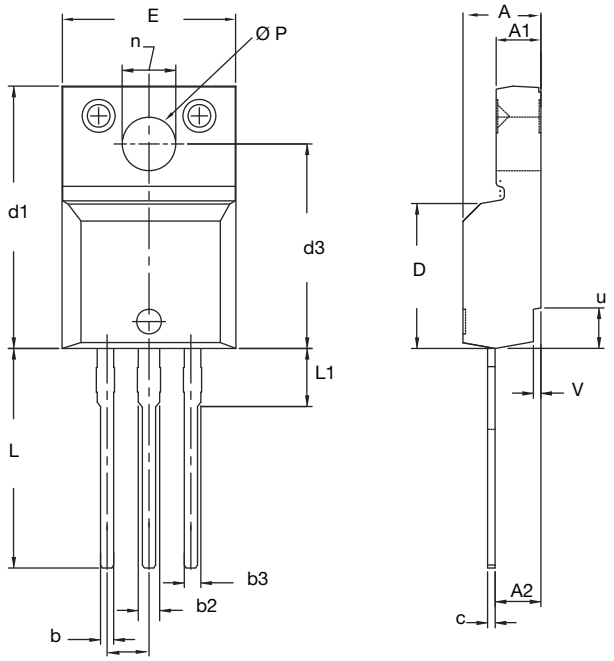



| | MILLIMETERS | | |
|---|---|---|---|
| **DIM.** | **MIN.** | **NOM.** | **MAX.** |
| A | 4.60 | 4.70 | 4.80 |
| b | 0.70 | 0.80 | 0.91 |
| b1 | 1.20 | 1.30 | 1.47 |
| b2 | 1.10 | 1.20 | 1.30 |
| C | 0.45 | 0.50 | 0.63 |
| D | 15.80 | 15.87 | 15.97 |
| e | | 2.54 BSC | |
| E | 10.00 | 10.10 | 10.30 |
| F | 2.44 | 2.54 | 2.64 |
| G | 6.50 | 6.70 | 6.90 |
| L | 12.90 | 13.10 | 13.30 |
| L1 | 3.13 | 3.23 | 3.33 |
| Q | 2.65 | 2.75 | 2.85 |
| Q1 | 3.20 | 3.30 | 3.40 |
| Ø R | 3.08 | 3.18 | 3.28 |

**Notes**

1. To be used only for process drawing
2. These dimensions apply to all TO-220 FULLPAK leadframe versions 3 leads
3. All critical dimensions should C meet $C_{pk} > 1.33$
4. All dimensions include burrs and plating thickness
5. No chipping or package damage
6. Facility code will be the 1st character located at the 2nd row of the unit marking

## OPTION 2: FACILITY CODE = Y




| | MILLIMETERS | | INCHES | |
|---|---|---|---|---|
| **DIM.** | **MIN.** | **MAX.** | **MIN.** | **MAX.** |
| A | 4.570 | 4.830 | 0.180 | 0.190 |
| A1 | 2.570 | 2.830 | 0.101 | 0.111 |
| A2 | 2.510 | 2.850 | 0.099 | 0.112 |
| b | 0.622 | 0.890 | 0.024 | 0.035 |
| b2 | 1.229 | 1.400 | 0.048 | 0.055 |
| b3 | 1.229 | 1.400 | 0.048 | 0.055 |
| c | 0.440 | 0.629 | 0.017 | 0.025 |
| D | 8.650 | 9.800 | 0.341 | 0.386 |
| d1 | 15.88 | 16.120 | 0.622 | 0.635 |
| d3 | 12.300 | 12.920 | 0.484 | 0.509 |
| E | 10.360 | 10.630 | 0.408 | 0.419 |
| e | 2.54 BSC | | 0.100 BSC | |
| L | 13.200 | 13.730 | 0.520 | 0.541 |
| L1 | 3.100 | 3.500 | 0.122 | 0.138 |
| n | 6.050 | 6.150 | 0.238 | 0.242 |
| Ø P | 3.050 | 3.450 | 0.120 | 0.136 |
| u | 2.400 | 2.500 | 0.094 | 0.098 |
| V | 0.400 | 0.500 | 0.016 | 0.020 |
| ECN: E19-0180-Rev. D, 08-Apr-2019<br>DWG: 5972 | | | | |

**Notes**

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3. All critical dimensions should C meet $C_{pk} > 1.33$
4. All dimensions include burrs and plating thickness
5. No chipping or package damage
6. Facility code will be the 1st character located at the 2nd row of the unit marking

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